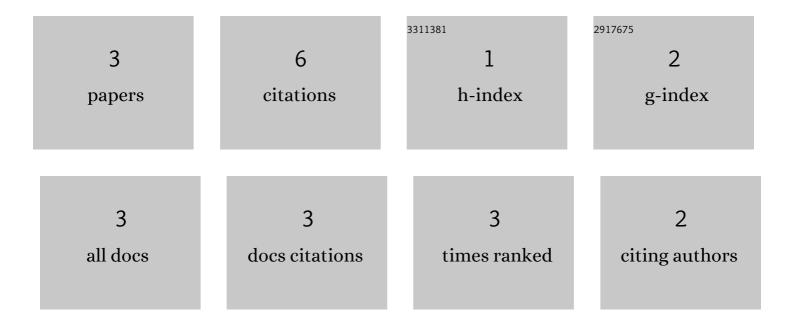
## Hung-Wei Chen

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/1203057/publications.pdf Version: 2024-02-01



#	Article	IF	CITATIONS
1	Research on ESD Protection of Ultra-High Voltage nLDMOS Devices by Super-Junction Engineering in the Drain-Side Drift Region. IEEE Journal of the Electron Devices Society, 2021, 9, 763-773.	2.1	0
2	Drain Side Area-Modulation Effect of Parasitic Schottky Diode on ESD Reliability for High Voltage P-Channel Lateral-Diffused MOSFETs. IEEE Electron Device Letters, 2021, 42, 1512-1515.	3.9	2
3	ESD Improvements on Power N-Channel LDMOS Devices by the Composite Structure of Super Junctions Integrated With SCRs in the Drain Side. IEEE Journal of the Electron Devices Society, 2020, 8, 864-872.	2.1	4